

isc Silicon NPN Power Transistor

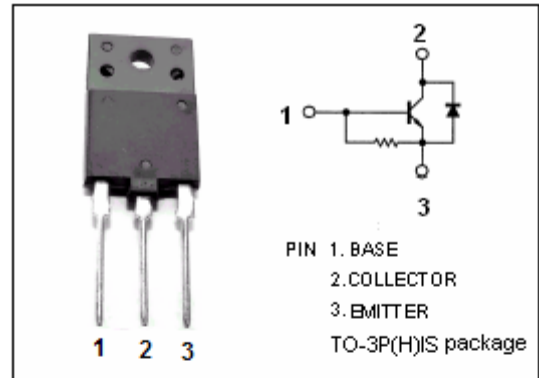
BU2725DX

DESCRIPTION

- High Switching Speed
- High Voltage
- Built-in Ddamper Ddiode

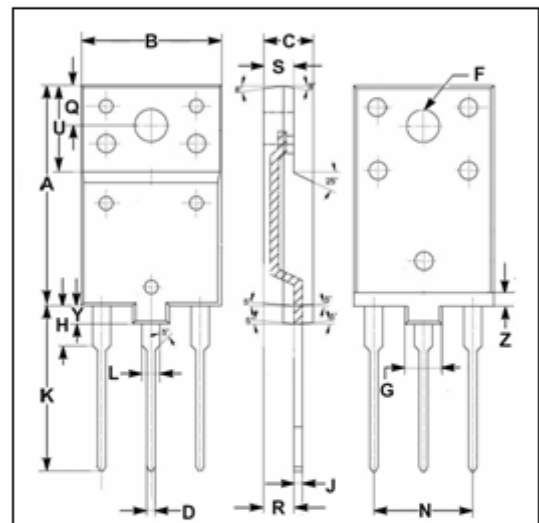
APPLICATIONS

- Designed for use in horizontal deflection circuits of color TV receivers.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CES}	Collector- Emitter Voltage(V _{BE} = 0)	1700	V
V _{EBO}	Emitter-Base Voltage	7.5	V
I _C	Collector Current- Continuous	12	A
I _{CM}	Collector Current-Peak	30	A
I _B	Base Current- Continuous	12	A
I _{BM}	Base Current-Peak	20	A
P _C	Collector Power Dissipation @ T _C =25°C	45	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C



DIM	mm	
	MIN	MAX
A	24.30	24.70
B	15.20	15.80
C	5.20	5.80
D	0.65	0.85
F	3.30	3.90
G	3.90	4.10
H	4.30	4.70
J	0.80	1.00
K	18.30	18.70
L	1.90	2.10
N	10.70	11.10
Q	4.40	4.60
R	3.30	3.70
S	3.20	3.40
U	9.50	9.70
Y	1.90	2.10
Z	1.40	1.60

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	2.8	°C/W

isc Silicon NPN Power Transistor**BU2725DX****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=600\text{mA}; I_C=0$	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=7\text{A}; I_B=1.75\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=7\text{A}; I_B=1.75\text{A}$			0.95	V
I_{CES}	Collector Cutoff Current	$V_{CE}=1700\text{V}; V_{BE}=0$ $V_{CE}=1700\text{V}; V_{BE}=0; T_C=125^{\circ}\text{C}$			1.0 2.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7.5\text{V}; I_C=0$		110		mA
h_{FE-1}	DC Current Gain	$I_C=1\text{A}; V_{CE}=5\text{V}$		19		
h_{FE-2}	DC Current Gain	$I_C=7\text{A}; V_{CE}=1\text{V}$	3.8		7.8	
V_{ECF}	C-E Diode Forward Voltage	$I_F=7\text{A}$			2.2	V